CONGRUENT VAPORIZATION IN THE V-SI SYSTEM AS STUDIED BY HIGH TEMPERATURE. (U) STATE UNIV OF NEW YORK AT BINGHAMTON DEPT OF CHEMISTRY C E MYERS ET AL. 26 NOV 85 TR-4 N00014-82-K-0501 F/G 7/4 ÁD-A162 285 1/1 UNCLASSIFIED



MICROCOPY RESOLUTION TEST CHART
NATIONAL BUREAU OF STANDARDS-1963-A



SECORITY CLASSIES AND			
	REPORT DOCUM	MENTATION PAGE	
- 1400 005		16. RESTRICTIVE MARKI	NGS
AD-A162 285		3. DISTRIBUTION / AVAIL	ABIUM SO CONTROL Has been approved
20. DECLASSIFICATION / DOWNGRADING SCHEDU	LE	Unlimited	for public release and sale; its distribution is unlimited.
4. PERFORMING ORGANIZATION REPORT NUMBE	R(S)	5. MONITORING ORGAN	IZATION REPORT NUMBER(S)
TR-4			
6a. NAME OF PERFORMING ORGANIZATION 6b. OFFICE SYMBOL		7a. NAME OF MONITOR	ING ORGANIZATION
C.E. Myers, Chem. Dept., State Univ. of NY, Univ. Ctr., at Bin	(If applicable) shamton	Office of Nav	al Research
6c. ADDRESS (City, State, and ZIP Code)		7b. ADDRESS (City, State, and ZIP Code)	
Binghamton, NY 13901		800 North Quincy Street Arlington, VA 22217	
8a. NAME OF FUNDING/SPONSORING ORGANIZATION (If applicable) Same as 7a		9. PROCUREMENT INSTR	UMENT IDENTIFICATION NUMBER
		N00014-8K-K-0501	
8c. ADDRESS (City, State, and ZIP Code)		10. SOURCE OF FUNDIN	G NUMBERS
Same as 7B		PROGRAM PROJECTION NO.	TASK WORK UNIT ACCESSION NO NR625-827
11 TITLE (Include Security Classification) Cong	ruent Vaporizat erature Knudsen	ion in the V-Si S Cell Mass Spectr	ystem as Studied by High ometry
12 PERSONAL AUTHOR(S) Clifford E. My	ers and Robert .	J. Kematick	
13a TYPE OF REPORT 13b. TIME C Technical FROM		14. DATE OF REPORT (Ye November 26, 1	ar, Month, Day) 15. PAGE COUNT 5
16. SUPPLEMENTARY NOTATION <u>Proceedin</u> <u>Topics</u> , American Association	gs, 33rd Annual for Mass Spect	Conference on Ma rometry, San Dieg	ss Spectrometry and Allied o, CA May 26-31, 1985
17. COSATI CODES	18. SUBJECT TERMS (Continue on reverse if ne	cessary and identify by block number)
FIELD GROUP SUB-GROUP Validation t		Continue on reverse if necessary and identify by block number) ides, V ₃ Si, V ₅ Si ₃ , vaporization behavior, hermodynamics activities, free energy of forma-	
	tion, enthalpy	of formation, co	ngruent vaporization, Knudsen
19. ABSTRACT (Continue on reverse if necessary			
The vaporization behavior of	vanadium silic	ides has been inv	estigated by Knudsen cell
mass spectrometry in the tem	perature range	1800-2000K. It w	as demonstrated that at
about 1900-2000K the congrue			
region. Thermodynamic activ direct comparison. Free ene	ities relative	to the solid elem	ents were obtained by
V ₅ Si ₃ (s) were calculated fro			
agreement with data obtained	elsewhere.		
	ř)		JIIC_
DTIC FILE COPY			DEC 1 0 1985
20. DISTRIBUTION/AVAILABILITY OF ABSTRACT		21. ABSTRACT SECURITY	CLASSIFICATION
☐UNCLASSIFIED/UNLIMITED 🖼 SAME AS	RPT. DTIC USERS	UNCLASSIFIED	
222 NAME OF RESPONSIBLE INDIVIDUAL		22b. TELEPHONE (Include	Area Code) 22c. OFFICE SYMBOL

OFFICE OF NAVAL RESEARCH

Contract N00014-82-K-0501

TECHNICAL REPORT NO. 4

CONGRUENT VAPORIZATION IN THE V-Si SYSTEM AS STUDIED BY
HIGH TEMPERATURE KNUDSEN CELL MASS SPECTROMETRY

bу

Clifford E. Myers and Robert J. Kematick
Department of Chemistry
State University of New York
University Center at Binghamton
Binghemton, NY 13901

Prepared for Publication

in

Proceedings, 33rd Annual Conference on Mass Spectrometry Accesion For and Allied Topics American Association for Mass Spectrometry NTIS C San Diego, CA DTIC T May 26-31, 1985 Ulanter . . . : Jestification Dut.ibution/ Availability Codes November 26, 1985 Avail and for Dist Special Reproduction in whole or in part is permitted for

*This document has been approved for public release and sale; its distribution is unlimited.

any purpose of the United States Government

CONGRUENT VAPORIZATION IN THE V-Si SYSTEM AS STUDIED BY HIGH TEMPERATURE KNUDSEN CELL MASS SPECTROMETRY*

Clifford E. Myers and Robert J. Kematick
Department of Chemistry
State University of New York at Binghamton
Binghamton, NY 13901

The vanadium silicides are of interest as corrosion resistant materials and for their potential applications in the electronics industry. In addition, their cohesive energies may be used, together with those of other silicides and related compounds, to assess factors affecting the strengths of chemical bonds in these compounds. The compounds in the V-Si system (1) are V_3Si , V_5Si_3 , V_6Si_5 , and VSi_2 . Of these, only V_3Si has any significant range of homogeneity; V_6Si_5 is only stable above about 1160K (2). Several authors (1,3,4,5) have reviewed critically the published thermochemical data for the system. These reviews do not include a recent study (2) which employed. Knudsen cell-mass spectrometry. One result of this last work was a plot of log activity vs composition (activities relative to the respective pure solid elements) for both V and Si at 1650K. The activities of V and Si were observed to cross within the $V_{5}Si_{7}$ phase region which, in consideration of the vapor pressures of pure V and Si at this temperature, led to the tentative conclusion that V_5Si_3 vaporized congruently (i.e. vapor and condensed phase have same composition). The goal of the present work was to test this conclusion.

EXPERIMENTAL

The samples were prepared by arc melting weighed mixtures of the elements and were characterized by X-ray powder diffraction.

Selected residues were analyzed by wet chemical techniques, and these results agreed closely with the compositions inferred from the original weights of V and Si. The mass spectrometer used was a 90° sector, single focusing, high resolution magnetic deflection instrument manufactured by Nuclide Corporation. The sample was placed in a tungsten metal cup within a tungsten metal effusion cell which was heated by radiation from a tungsten helix resistance heating element. The entire furnace assembly was surrounded by tungsten and tantalum radiation shields within a water cooled vacuum enclosure. Temperatures were measured with a tungsten-rhenium thermocouple inserted into the base of the effusion cell; the thermocouple was calibrated by means of an optical pyrometer sighted through the orifice into the interior of the effusion cell. The design of the mass spectrometer was such that the molecular beam from the effusion cell, the path of the ionizing electrons, and the ion beam were all mutually perpendicular. Silicon signals were obtained with ionizing electron energies of 12.5 eV in order to minimize the effects of the mass 28 background. An ionizing energy of 30.0 eV was used for the vanadium data.

RESULTS

Thermodynamic activities relative to the pure solid elements were obtained as follows. The partial pressure of a species in a Knudsen cell-mass spectrometry experiment is proportional to IT, where I is the ion current due to that species and T is the temperature of the effusing vapor. Hence the thermodynamic activity of a species in the sample is given by $a = I/I^{\circ}$, where I

is measured for the element above the sample and I° is measured above the pure element under the same experimental conditions of temperature, orifice area, and electron energy (2). Although I and I° are measured in different experiments, the mass spectrometer is sufficiently stable that reproducible results are obtained. In practice, activities at a given temperature were calculated from slopes and intercepts of log IT and log I°T vs 1/T plots. The activities at a given composition and temperature were used to calculate the free energies of phase formation:

$$(1-x)V(s) + xSi(s) \approx V_{1-x}Si_x(s)$$

 $\Delta G_{1}^{0}/R = 2.303 \text{ T Log a}_{V}^{(1-x)} a_{S_{1}}^{x}$

Control of the Contro

where x is the atom fraction of Si. Entropy and heat capacity data for the silicides cited or estimated by Smith (1) were used, together with Smith's data (6) for V and data from the JANAF Tables (7), to calculate $\Delta G_{P}^{Q}/R$ as a function of temperature and ΔH_{ϕ}^{O} ,298.15/R from the experimental data. As shown in Table 1, agreement with the results of the earlier mass spectrometric study (2) is quite good. Samples richer in Si than V_5Si_3 were found preferentially to lose Si and samples richer in V than V_3Si were found preferentially to lose V. Hence there is at least one congruently vaporizing composition in the $V_3Si-V_5Si_3$ composition range. The results from X-ray powder diffraction were ambiguous in that it was very difficult to identify lines attributable to V_3Si , even in samples which were well within the $V_3Si-V_5Si_3$ twophase region. However, wet chemical analysis before and after vaporization of a significant fraction (19-58%) showed clearly that, at about 1900-2000K, there is only one congruently vaporizing composition which is within the V_3Si single-phase

region. The precise composition is difficult to fix since, near the congruently vaporizing composition, the partial pressures of V and Si differ only very slightly from those at congruency. Hence, to reach congruency it is necessary to vaporize a major fraction of the sample. It should be noted that this congruent vaporization is for <u>effusion</u> conditions. Hence partial pressures differ from those under <u>static</u> conditions since Si effuses more rapidly than V. It is not yet clear whether the congruently vaporizing composition under static conditions lies within $V_3 Si$ or $V_5 Si_3$.

REFERENCES

- 1. J. F. Smith, Bull. Alloy Phase Diagrams, 2, 42 (1981).
- 2. E. K. Storms and C. E. Myers, High Temp. Science, in press.
- 3. T. G. Chart, Natl. Phys. Lab. (UK) Rep. 18 (1972).
- 4. T. G. Chart, High Temp. High Press., 5, 241 (1973).
- 5. P. F. Freund and K. E. Spear, J. Less-Common Met., 60, 185 (1978).
- 6. J. F. Smith, Bull. Alloy Phase Diagrams, 2, 40 (1981).
- 7. D. R. Stull and H. Prophet, NSRDS-NBS No. 37 (1971).
- *Supported in part by the U. S. Office of Naval Research.

TABLE 1
THERMODYNAMIC DATA FOR V. ADIUM SILICIDES

		ΔG ^Q ,1650K/R	(kK)
1/4	v ₃ si	3.63	Si and V activities (22 a/o Si)
		4.35	Si and V activities, $V_5Si_3 + V_3Si$
		4.40	Storms and Myers (2), $V_5Si_3 + V_3Si$
1/8	v ₅ si ₃	5.49	Si and V activities, $V_5Si_3 + V_3Si$
		5.47	Storms and Myers (2), $V_5Si_3 + V_3Si$
		ΔH ^Q ,298.15/R	(kK)
1/4	v ₃ si	5.35	Si and V activities, $V_5Si_3 + V_3Si$
		5.40	Storms and Myers (2), $V_5Si_3 + V_3Si$
		5.18	Smith (1)
			•
1/8	v ₅ si ₃	6.33	Si and V activities, $V_5Si_3 + V_3Si$
		6.31	Storms and Myers (2), $V_5Si_3 + V_3Si$

END

FILMED

1-86

DTIC